

In the Claims:

Please cancel claims 1-12 and 17-20 without prejudice or disclaimer.

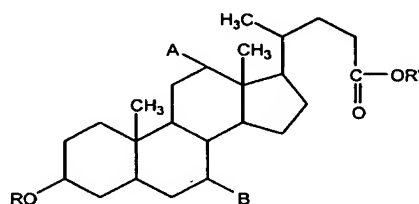
Please add new claims 21-28, as follows:

Claims 1-12 (currently canceled)

Claim 13 (currently amended) A resist flow process for forming a photoresist pattern comprising the steps of:

(a) forming a first photoresist pattern on a substrate using a photoresist composition comprising a photoresist polymer, a photo acid generator, an organic solvent, and an additive of following Formula 1:

Formula 1



wherein, A is H or -OR'',

B is H or -OR''', and

R, R', R'' and R''' are independently selected from the group consisting of C1-C10 alkyl, C1-C10 alkoxyalkyl, C1-C10 alkylcarbonyl, and C1-C10 alkyl containing at least one hydroxyl group (-OH),

and

(b) producing a second photoresist pattern from said first photoresist pattern using a resist flow process.

Claim 14 (currently amended) The resist flow process according to of claim 13, wherein said step (a) further comprises the steps of:

- (i) coating said photoresist composition on said substrate to form a photoresist film, wherein said substrate is a semiconductor device; and
- (ii) producing said first photoresist pattern using a lithography process.

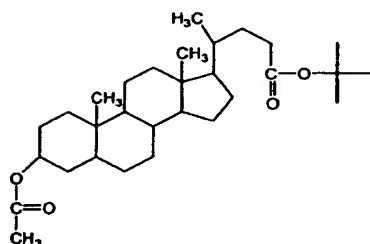
Claim 15 (currently amended) The resist flow process according to of claim 13, wherein said first and second photoresist pattern comprises a contact hole pattern.

Claim 16 (currently amended) The resist flow process according to of claim 13, wherein said resist flow process comprises heating said first photoresist pattern to temperature in the range of from 120 to 190°C.

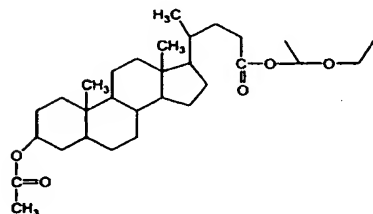
Clams 17-20 (currently canceled)

Claim 21 (new) The resist flow process according to claim 13, wherein said additive is selected from the group consisting of compounds of following Formulas 2 to 7:

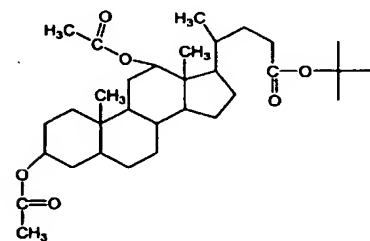
Formula 2



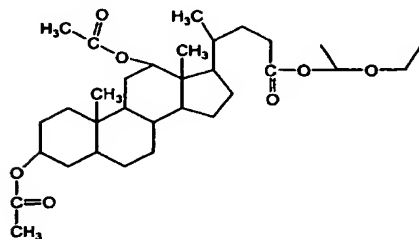
Formula 3



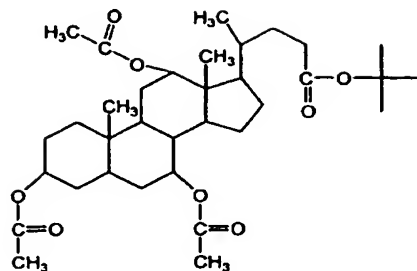
Formula 4



Formula 5

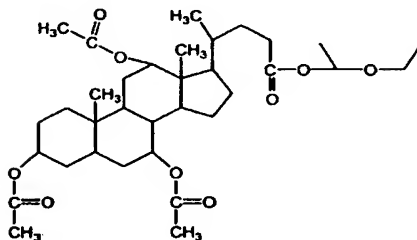


Formula 6



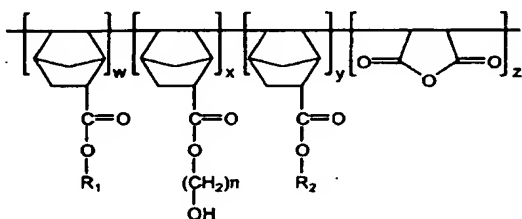
, and

Formula 7

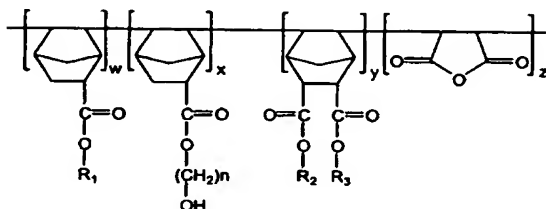


Claim 22 (new) The resist flow process according to claim 13, wherein said photoresist polymer is a compound of following Formulas 8 or 9:

Formula 8



Formula 9



wherein, R1 is and acid labile protecting group;

R2 is hydrogen;

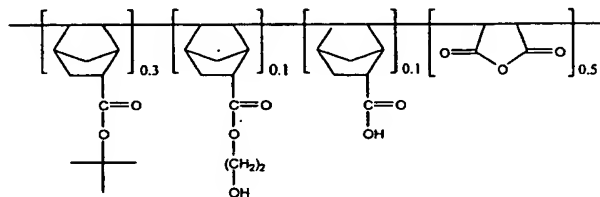
R3 is hydrogen, selected from the group consisting of C1-C10 alkyl, C1-C10 alkoxyalkyl, and C1-C10 alkyl containing at least one hydroxyl group (-OH);

n is an integer from 1 to 5; and

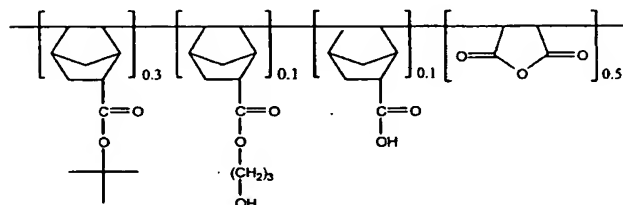
w, x, y and z individually denote the mole ratio of each monomer, preferably with proviso that $w + x + y = 50\text{mol}\%$, and z is $50\text{mol}\%$.

Claim 23 (new) The resist flow process according to claim 13, wherein said photoresist polymer is selected from the group consisting of compounds of following Formulas 10 to 13:

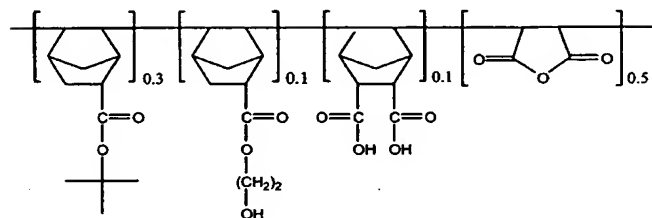
Formula 10



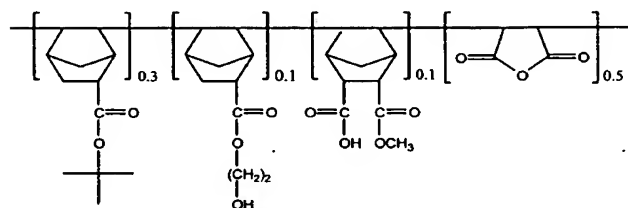
Formula 11



Formula 12



Formula 13



Claim 24 (new) The resist flow process according to claim 13, wherein said additive is present in an amount ranging from 1 to 70% by weight of the photoresist polymer.

Claim 25 (new) The resist flow process according to claim 13, wherein said photoacid generator is selected from the group consisting of diphenyl iodide hexafluorophosphate, diphenyl iodide hexafluoroarsenate, diphenyl iodide hexafluoroantimonate, diphenyl p-methoxyphenyl triflate, diphenyl p-toluenyl triflate, diphenyl p-isobutylphenyl triflate, diphenyl p-tert-butylphenyl triflate, triphenylsulfonium hexafluorophosphate, triphenylsulfonium hexafluoroarsenate, triphenylsulfonium hexafluoroantimonate, triphenylsulfonium triflate, dibutyl-naphthylsulfonium triflate, and mixtures thereof .

Claim 26 (new) The resist flow process according to claim 13, wherein said photoacid generator is present in an amount ranging from 0.01 to 10% by weight of the photoresist polymer.

Claim 27 (new) The resist flow process according to claim 13, wherein said organic solvent is selected from the group consisting of propyleneglycol methyl ether acetate, ethyl lactate, methyl 3-methoxypropionate, ethyl 3-ethoxypropionate and cyclohexanone.

Claim 28 (new) The resist flow process according to claim 13, wherein said organic solvent is present in an amount ranging from 100 % to 1000% by weight of the photoresist polymer.